



(43) International Publication Date
10 March 2005 (10.03.2005)

PCT

(10) International Publication Number
WO 2005/022617 A1

- (51) **International Patent Classification⁷:** H01L 21/033, 21/308, 21/311, 21/266

(21) **International Application Number:** PCT/US2004/026517

(22) **International Filing Date:** 12 August 2004 (12.08.2004)

(25) **Filing Language:** English

(26) **Publication Language:** English

(30) **Priority Data:** 10/652,174 22 August 2003 (22.08.2003) US

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(81) **Designated States (unless otherwise indicated, for every kind of national protection available):** AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

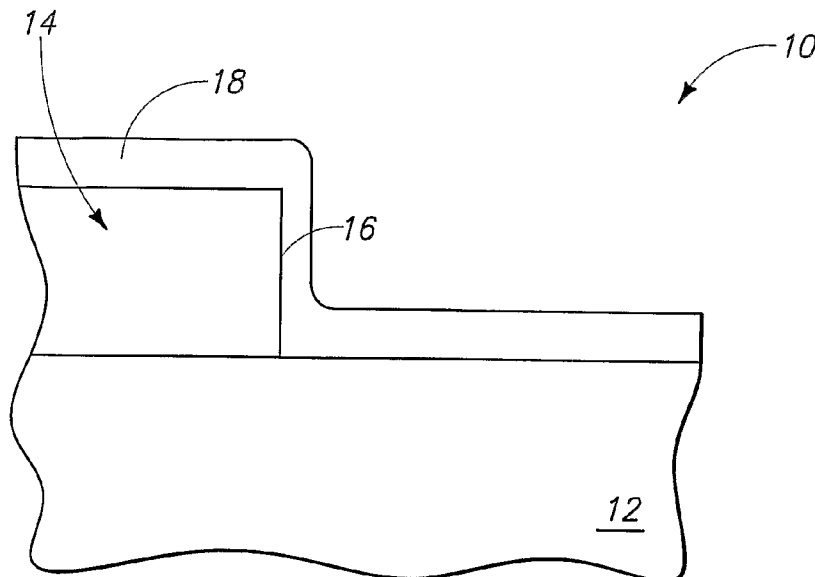
(84) **Designated States (unless otherwise indicated, for every kind of regional protection available):** ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— with international search report

Published:
— *with international search report*

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(54) Title: MASKING METHODS



(57) Abstract: The invention includes masking methods. In one implementation, a masking material comprising boron doped amorphous carbon is formed over a feature formed on a semiconductor substrate. The masking material comprises at least about 0.5 atomic per cent boron. The masking material is substantially anisotropically etched effective to form an anisotropically etched sidewall spacer comprising the boron doped amorphous carbon on a sidewall of the feature. The substrate is then processed proximate the spacer while using the boron doped amorphous carbon comprising spacer as a mask. After processing the substrate proximate the spacer, the boron doped amorphous carbon comprising spacer is etched from the substrate. Other implementations and aspects are contemplated.



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